



Development of rugged hydrogen sensors for measuring charge-exchange neutral flux at the wall and divertor

Ryan Hood¹, R. Kolasinski¹, D. Truong¹, J. Whaley¹, D. Rudakov², T. Abrams³, J. Watkins¹, A. Talin¹



¹Sandia National Laboratories, Livermore, CA

²University of California, San Diego, La Jolla, CA

³General Atomics, San Diego, CA





Sandia National Laboratories is a multimission laboratory managed and operated by National Technology & Engineering Solutions of Sandia, LLC, a wholly owned subsidiary of Honeywell International Inc., for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525.

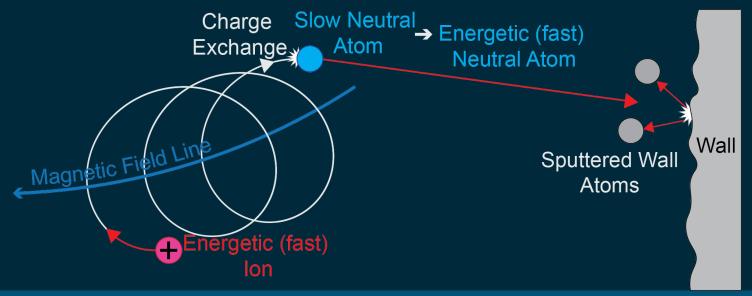
Materials will be a significant challenge for future tokamaks





Exposure conditions:

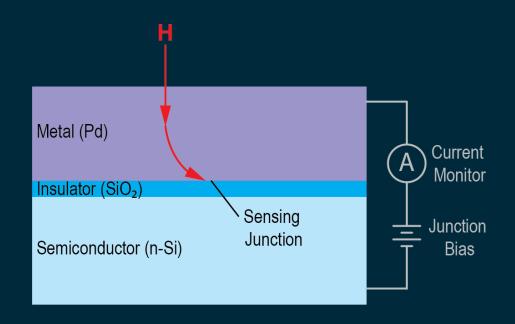
- High-flux D-T plasmas
- High-energy fusion products (14 MeV n, helium ash)
- Impurities
- Charge-exchange neutrals
 - Diagnostics are presently lacking on US Tokamaks
 - In past, low energy neutral analyzers and carbon resistance probes have been used
 - Pd-MIS style sensors may be better choice compact and can be regenerated [1]

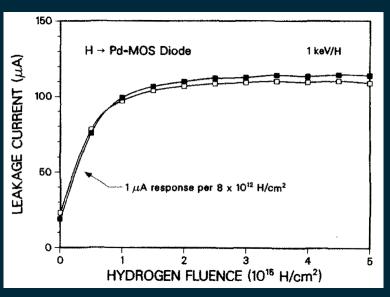




Metal – semiconductor junction forms a Schottky diode

- In reverse bias, leakage current is exponentially related to the barrier height
- Implanted hydrogen rapidly diffuses to the Pd-SiO₂ interface, where the hydrogen is weakly trapped, changing the barrier height
- Hydrogen is detected by monitoring the reverse current

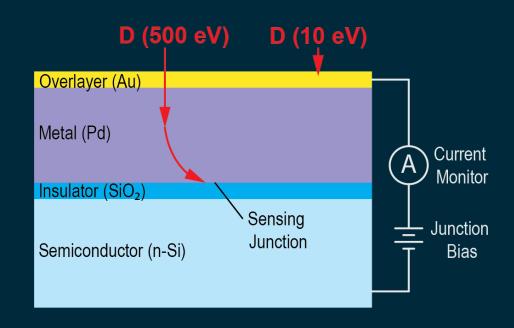




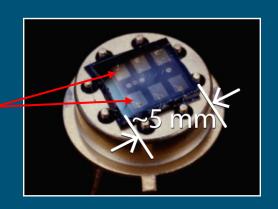
R. Bastasz, B.L. Cain, T.E. Cayton, R.C. Hughes, and D.N. Ruzic, J. Nucl. Mater. 162-164 (1989) 587

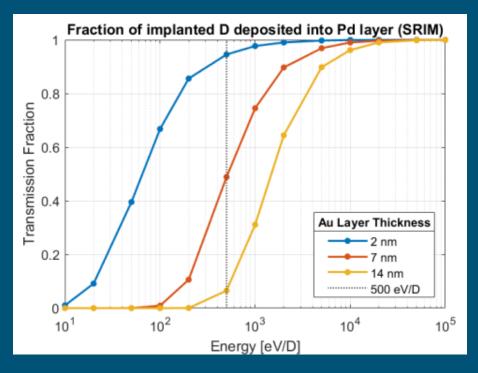
Energy resolution provided by gold overlayer

- Thin Au coatings can be deposited on different sensors to provide energy discrimination
- D₂ not penetrating the Au layer can not reach the SiO₂ interface
- Requires modelling to interpret (assume Maxwellian energy distribution + SRIM to estimate ion range)









Design modifications to improve ruggedness

High energy particles result in charge accumulation in the oxide layer

- This shifts the barrier potential making sensor calibration impossible

Current Monitor

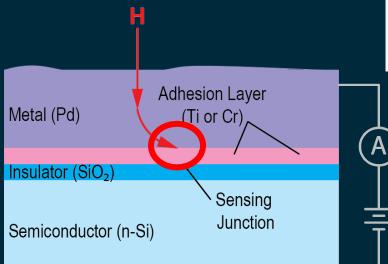
Junction

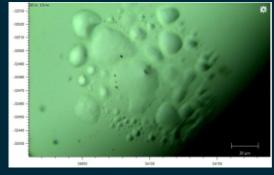
Bias

Remedies:

Minimize oxide thickness

- Must be grown slowly with careful surface preparation
- Done at Sandia MESA facility





Maximize metal layer thickness (~500 nm) • Thick layers (greater than ~ 50)

- Thick layers (greater than ~ 50 nm) result in poor fabrication yields
- Adhesion layer would typically be used in this situation (Ti/Cr), but this blocks H from reaching junction

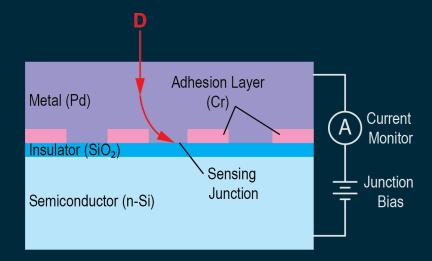


Patterned adhesion layer enables H sensing with thick Pd layer



Adhesion layer is deposited through a fine hole pattern

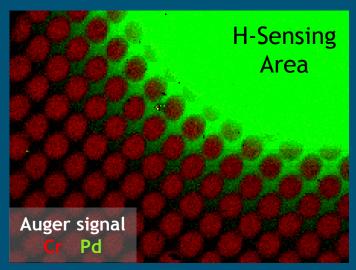
- Hydrogen still has access to junction
- With improved bond between Pd and SiO₂



Newest sensors have 500 nm Pd Expected to withstand c-x energies up to ~50 keV based on SRIM calculations (30x improvement)

Good compromise





Auger electron microscopy map showing elemental composition on surface

Sensors conditioned using D ion beam before testing in DIII-D tokamak

1.5 KeV D⁺



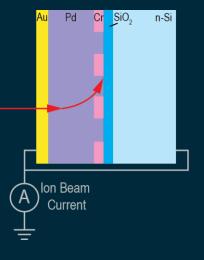
Conditioning performed using SIMS ion beam

- Precision dosing by measuring collected ion current
- Control of beam energy and sensor temperature

7 nm Au, patterned Cr sensor test

1500 eV/D exposure 6
1500 eV/D exposure 7
340 eV/D exposure 8
340 eV/D exposure 9

100
101
101
101
101
1015
1016
1017
Dose [D/cm²]



- Strong response (~ 1-10 uA)
- Consistent response to dose after ~ 4 regeneration cycles
- Different ion energies give different response
 - Fewer ions penetrate gold layer at lower energy
 - More reflected ions at lower energy

SIMS ion beam station at Sandia National Laboratories





TO-5 mounted sensor

Sensors were tested at DIII-D tokamak in piggyback experiments (June 2021)

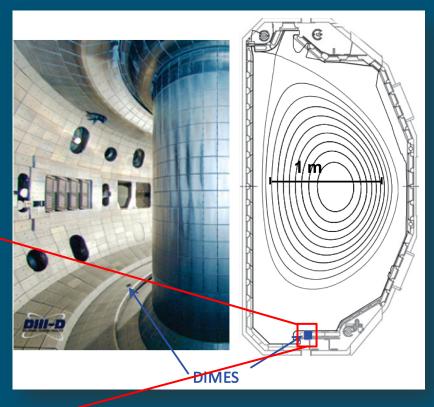


Sensors were mounted in Divertor Material Evaluation System (DiMES) and tested over several days

- Test of sensors and data collection system in the tokamak environment
- Same gold thickness on each sensor (7 nm Au)







Adapted from: Rudakov D., et al., Fusion Eng. Des., 124 (2017), pp. 196-201



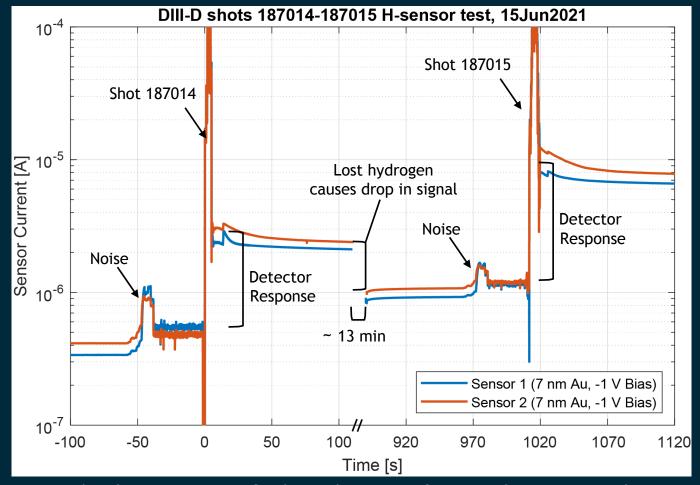
Sensors were successfully demonstrated in tokamak environment



Sensors exposed to ~ 27 plasma shots over 2 days*

- Saturation after ~ 3 H-mode shots in USN configuration – strong signal!
- Demonstrated sensor regeneration with thermal cycling
- Nearly identical response from pair of sensors in USN configuration before saturation

If we assume 500 eV thermal c-x particles: ~ 5 x 10¹⁴ D/cm² s



H-sensor data from consecutive USN plasma shots in DiMES, starting from regenerated state



^{*} Special thanks to Huigian Wang for allowing us to piggyback during his experiment

Post-exposure analysis shows dust and signs of erosion



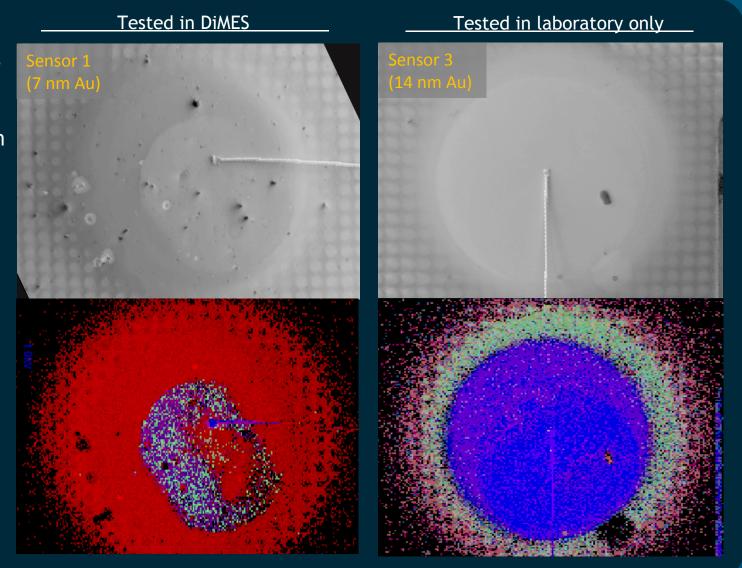
Scanning electron microscope images

- Sensors exposed in DiMES show dust and mark where aperture was aligned
- Sensors only tested in lab are nearly blemish free

Auger electron microscopy maps show elemental composition on surface (~0.4 – 5 nm)

Carbon Palladium Gold

- Sensors exposed in DiMES are covered in carbon from cap except under aperture
- Sensors only tested in lab look as expected



Successful demonstration at DIII-D paves way for future development and testing



Summary

- Ruggedized H-sensors have been developed with thin oxide and thick Pd for resilience to high energy particles
- Sensors were demonstrated in DiMES at the DIII-D Tokamak withstanding ~27 plasma shots

Future Work

- Explore optimization of adhesion layer
- Continue laboratory testing of sensors
- Further testing at DIII-D
 - Measurements of shot-to-shot energy distribution and fluence using multiple gold thicknesses
 - Resolve poloidal distribution of c-x flux using multiple sensors with angled apertures
 - Integration into WITS wall station



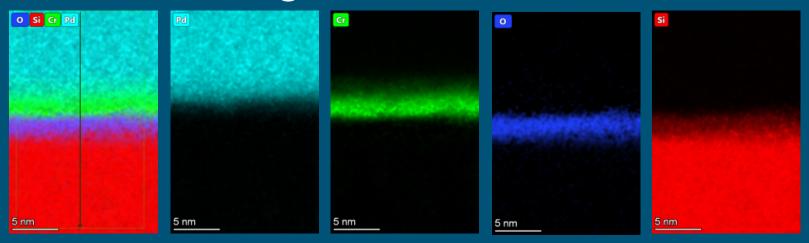


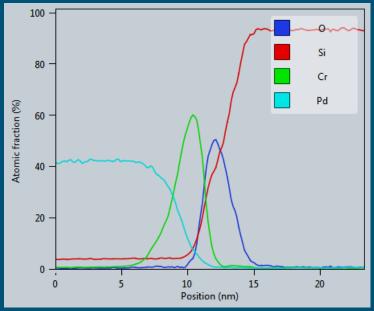
Supplemental slides

1

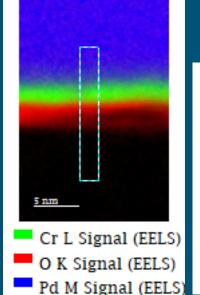
EDS and EELS measurements show minimal intermixing or oxidation of Cr



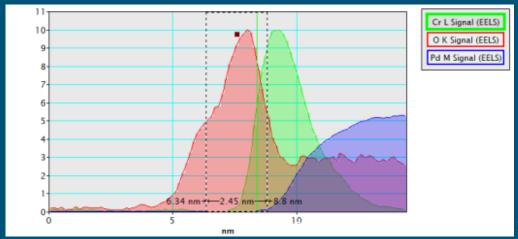


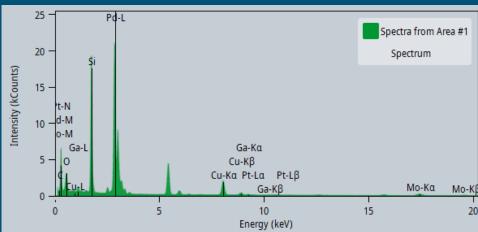


EDS measured 2.8 nm thick for Cr and 2.5 nm thick for oxide



EELS suggests something more like 2.5 nm for both the Cr and the O layer



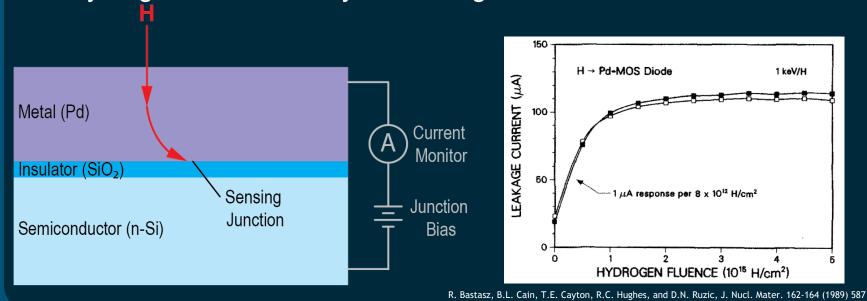


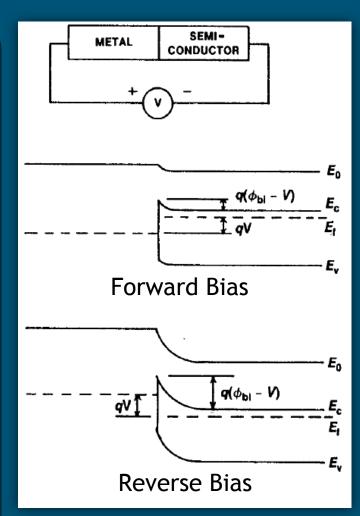
EDS and EELS measurements by J. Sugar

14 Pd-MIS H-sensor operating principle

Metal – semiconductor junction forms a Schottky diode

- In reverse bias, leakage current is exponentially related to the barrier height
- Implanted hydrogen rapidly diffuses to the Pd-SiO₂ interface, where the hydrogen is weakly trapped changing the barrier height
- Hydrogen is detected by monitoring the reverse current





Metal-Semiconductor junction band diagrams shown in forward and reverse bias (oxide not shown for simplicity)